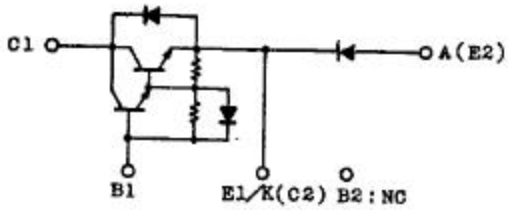
SEMICONDUCTOR
TECHNICAL DATA

MG100G1JL1
MG100G2CL1
MG100G2DL1



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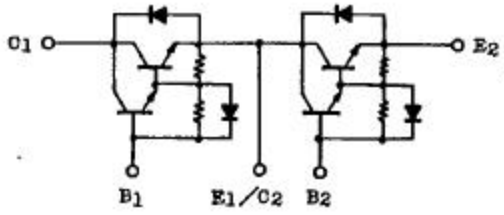
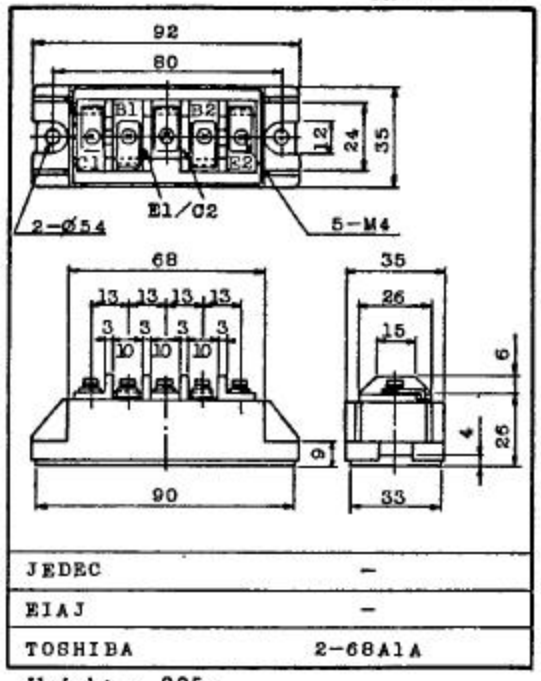


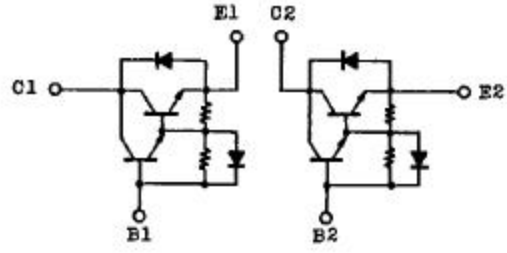
MG100G2CL1

Unit in mm



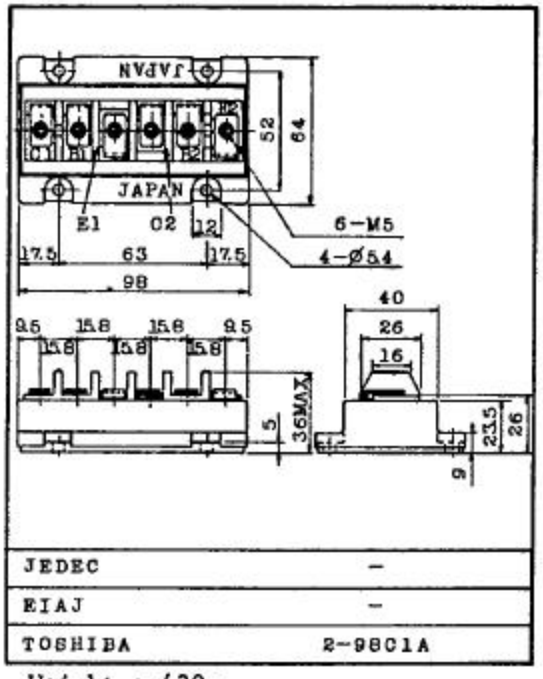
JEDEC	—
EIAJ	—
TOSHIBA	2-68A1A

Weight : 205g



MG100G2DL1

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	2-98C1A

Weight : 430g

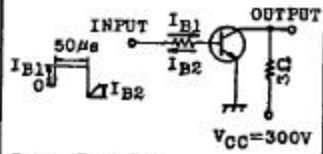
SEMICONDUCTOR
TECHNICAL DATA

MG100G1JL1
MG100G2CL1
MG100G2DL1

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	600	V
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	450	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current	DC	I_C	100	A
	1ms	I_C	200	
	DC	$-I_C$	100	
Base Current		I_B	5	A
Collector Power Dissipation (Tc=25°C)		P_C	400	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-40 ~ 125	°C
Isolation Voltage		VIsol	2500(AC 1 Minute)	V
Screw Torque (Terminal/Mounting)		-	20/30	kg.cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=600V, I_E=0	-	-	2.0	mA
Emitter Cut-off Current		I_{EBO}	V_{EB}=6V, I_C=0	-	-	200	mA
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	I_C=0.5A L=40mH	450	-	-	V
DC Current Gain		h_{FE}	V_{CE}=5V, I_C=100A	100	-	-	-
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=100A, I_B=2A	-	-	2.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$		-	-	2.7	V
Emitter-Collector Voltage		V_{ECO}	I_E=100A, I_B=0	-	-	1.6	V
Reverse Recovery Time		t_{rr}	$-I_C$=100A, V_{EB}=3V V_{CC}=300V, di/dt=100A/μs	-	-	2.0	μs
Collector Output Capacitance		Cob	V_{CB}=50V, I_E=0 f=1MHz	-	1000	-	pF
Switching Time	Turn-on Time	ton		-	-	2.0	μs
	Storage Time	tstg		-	-	12	
	Fall Time	tf	I_{B1}=-I_{B2}=2A DUTY CYCLE=0.5%	-	-	2.0	
Thermal Resistance (Junction to Case)		$R_{th(j-c)}$	Transistor	-	-	0.31	°C/W
			Diode	-	-	1.3	